DESCRIPTION	QTY
Standard metalorganic channel [MOG1] with 2 LOTO hand valves as customer interface; bubbler placed outside GMS cabinet *(1xTCS)*	1
Combined standard and dilution metalorganic channel [MOG1/G3-D] *(2xTMAl)*	1
Standard gas channel with pusher, for low flow [MOG2] *(1xNN, 1xHCl)*	2
Triple-Cascading standard gas channel with pusher [MOG2-T] *($3xC_3H_8$)*	1
Combined standard and dilution/dopant gas channel [MOG2/G4-D] *($2xN_2$)*	1

DESCRIPTION	QTY
Computer control system	1
MES interface SECS II/GEM for MOVPE systems (incl. router)	1

DESCRIPTION	QTY
Additional pusher for MO-G4 *(1xN_2)*	1
Carrier gas channel (Dummy line) for balancing gas flow switching *(1xR/V Center, 1xR/V Bottom)*	2
MO-differential run/vent pressure balancing *(1xMO, 1xR/V center)*	2
MO-Vac High Pressure Purge	1
Epison 5 *(1xTCS)*	1

DESCRIPTION	QTY
EpiCurve TT® AR 3W	1
Automatic Feed Forward incl. Autosat	1

DESCRIPTION	QTY
Spare provision for standard purifier HCl	1
Spare provision for standard purifier C_3H_8	1
Single Port Hygrometer incl. valve and housing (H_2/N_2)	2
Ar limiter	1

DESCRIPTION	QTY
AIX G5 WW C Planetary Reactor® for deposition on 8x150 mm wafers	1

Performance of the CVD system should result in the following materials specification:
(All measurements are for 150mm 4H-SiC, 4° off-axis wafers, i.e. excluding 5 mm from wafer edge)

The specifications are not meant to be the typical performance of the system.

Ref. No.	Parameter	Specification
1.	**Undoped 4H-SiC**	
1.1.	Growth rate (FTIR)	≥ 20 µm/h
1.2.	Thickness uniformity (FTIR)	σ/mean ≤ 2%
1.3.	Background doping level (CV)	≤ $8x10^{14}$ cm^{-3}
2.	**N_2-doped 4H-SiC ($1x10^{16}$ cm^{-3} doping level)**	
2.1.	Doping level (CV)	$1x10^{16}$ cm^{-3} ± 20%
2.2.	Doping uniformity (CV) on wafer	σ/mean ≤ 5%
3.	**n-type 4H-SiC (10 µm epi layer)**	
3.1.	Mean Thickness-uniformity wafer to wafer	σ/mean ≤ 1%
3.2.	Mean Doping uniformity wafer to wafer	σ/mean ≤ 3%
3.3.	Mean Thickness-uniformity run to run (for 24 wafers or 3 runs)	σ/mean ≤ 2%
3.4.	Mean Doping uniformity run to run (for 24 wafers or 3 runs)	σ/mean ≤ 4%
3.5.	Smooth Morphology (Zygo or 20 µm x 20 µm AFM)	RMS roughness < 1 nm
3.6.	Particle density for killer defects (downfall inclusions, carrots, triangular defects) > 10 µm, clustered defect are excluded; epi ready prime grade wafer	<0.4 defect/cm^2